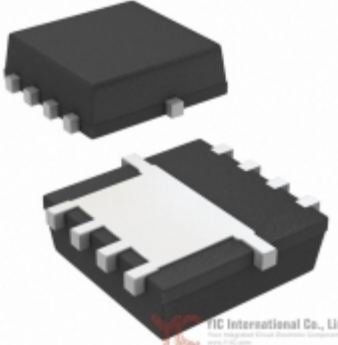



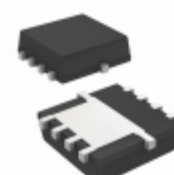
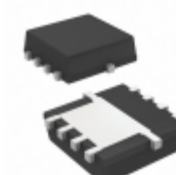
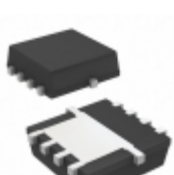


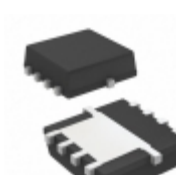
	<h2 style="color: red;">SI7812DN-T1-E3</h2>
	<b>Hersteller-Teilenummer:</b> <a href="#">SI7812DN-T1-E3</a>
	<b>Hersteller / Marke:</b> <a href="#">Electro-Films (EFI) / Vishay</a>
	<b>Teil der Beschreibung:</b> MOSFET N-CH 75V 16A 1212-8
	<b>Datenblätter:</b>  <a href="#">SI7812DN-T1-E3.pdf</a>
	<b>RoHs Status:</b> Bleifrei / RoHS-konform
	<b>Lagerzustand:</b> New original, 4000 pcs Stock Available.
	<b>Liefern von:</b> Hong Kong
	<b>Versandweg:</b> DHL/Fedex/TNT/UPS/EMS
<p>Image may be representation. See specs for product details.</p>	

### Spezifikationen

Teilenummer	<a href="#">SI7812DN-T1-E3</a>
Hersteller	<a href="#">Electro-Films (EFI) / Vishay</a>
Beschreibung	MOSFET N-CH 75V 16A 1212-8
Kategorie	<a href="#">Diskrete Halbleiterprodukte &gt; Transistoren-FETs,</a>
Teilstatus	4000 pcs Stock
detaillierte Beschreibung	N-Channel 75V 16A (Tc) 3.8W (Ta), 52W (Tc) Surface
Serie	TrenchFET®
Technologie	MOSFET (Metal Oxide)
Betriebstemperatur	-55°C ~ 150°C (TJ)
Befestigungsart	Surface Mount
Verpackung / Gehäuse	PowerPAK® 1212-8
Supplier Device-Gehäuse	PowerPAK® 1212-8
Verlustleistung (max)	3.8W (Ta), 52W (Tc)
Typ FET	N-Channel
FET-Merkmal	-
Drain-Source-Spannung (Vdss)	75V
Strom - Ununterbrochener Abfluss (Id) bei 25 ° C	16A (Tc)
Rds On (Max) @ Id, Vgs	37 mOhm @ 7.2A, 10V
VGS (th) (Max) @ Id	3V @ 250µA
Gate Charge (Qg) (Max) @ Vgs	24nC @ 10V
Eingabekapazität (Ciss) (Max) @ Vds	840pF @ 35V
Antriebsspannung (Max Rds On, Min Rds On)	4.5V, 10V
Vgs (Max)	±20V
Verpackung	Original-Reel®
Bleifreier Status / RoHS-Status	Lead free / RoHS Compliant
Feuchtigkeitsempfindlichkeitsniveau (MSL)	1 (Unlimited)
Andere Namen	SI7812DN-T1-E3DKR

SI7812DN-T1-E3 ist neu im Original, Suche SI7812DN-T1-E3 Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie SI7812DN-T1-E3 Electro-Films (EFI) / Vishay mit Garantie und Vertrauen. Anfrage SI7812DN-T1-E3: [Info@Y-IC.com](mailto:Info@Y-IC.com)

Sie können auch interessiert sein:

 <b>SI7811DN</b> SI SI7811DN SI	 <b>SI7810DN-T1-GE3</b> Vishay / Siliconix MOSFET N-CH 100V 3.4A 1212-8	 <b>SI7810DN-T1-E3</b> Vishay / Siliconix MOSFET N-CH 100V 3.4A 1212-8	 <b>SI7812DN-T1-GE3</b> Electro-Films (EFI) / Vishay MOSFET N-CH 75V 16A 1212-8 PPAK
 <b>SI7812DN-T1-GE3</b> Vishay / Siliconix MOSFET N-CH 75V 16A 1212-8 PPAK	 <b>SI7818DN</b> SI SI7818DN SI	 <b>SI7810DN-T1-GE3</b> Electro-Films (EFI) / Vishay MOSFET N-CH 100V 3.4A 1212-8	 <b>SI7818DN-T1-E3</b> Vishay / Siliconix MOSFET N-CH 150V 2.2A 1212-8

### heiße Teile

Mehr

SI7792DP-T1-GE3	SI7792DP-T1-GE3	SI7794DP-T1-GE3	SI7794DP-T1-GE3	SI7798DP-T1-GE3
SI7804DN	SI7804DN-T1-E3	SI7804DN-T1-E3	SI7806ADN	SI7806ADN-T1-E3
SI7806ADN-T1-E3	SI7806ADN-T1-E3-PBF	SI7806ADN-T1-GE3	SI7806ADN-T1-GE3	SI7806AEDN-T1-E3
SI7806BDN	SI7806BDN-T1-GE3	SI7806DN-T1-E3	SI7806DN-T1-GE3	SI7810DN
SI7810DN-T1	SI7810DN-T1-E	SI7810DN-T1-E3	SI7810DN-T1-E3	SI7812DN-T1-E3
SI7812DN-T1-GE3	SI7812DN-T1-GE3	SI7818DN-T1-E3	SI7818DN-T1-E3	SI7820DN-T1-E3
SI7820DN-T1-E3	SI7820DN-T1-GE3	SI7820DN-T1-GE3	SI7840BDP	SI7840BDP-T1-E3
SI7840BDP-T1-E3	SI7840BDP-T1-GE3	SI7840BDP-T1-GE3	SI7840DP	SI7840DP-T1
SI7840DP-T1-E3	SI7840DP-T1-GE3	SI7840DP-T1-GE3	SI7842DP	SI7842DP-T1-E3
SI7842DP-T1-E3	SI7842DP-T1-GE3	SI7842DP-T1-GE3	SI7844DP	SI7844DP-T1

Contact us:[Info@Y-IC.com](mailto:Info@Y-IC.com)

HINZUFÜGEN: Einheit A5-B5 Nr.509, 5 / F Sing Win Fabrikgebäude, 15-17 Shing Yip St, Kwun Tong, Kowloon, HongKong.

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